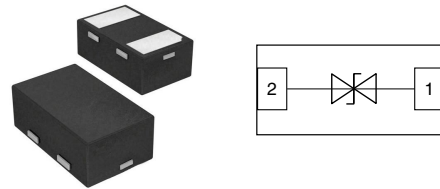


9 G8 'DfchYW]cb'8]cXY]b'DFN1006

: YUi fYg

- 80Watts peak pulse power ($T_p = 8/20\mu s$)
- DFN1006 package
- Bidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- Medium capacitance ($C_j = 15pF$ typ.)
- Protection one data/power line to:
 - IEC 61000-4-2 $\pm 30kV$ contact $\pm 30kV$ air
 - IEC 61000-4-4 (EFT) 40A (5/50ns)
 - IEC 61000-4-5 (Lightning) 7A (8/20 μs)



A YW Ub]WJ'8 UHJ

- 7 UgY. DFN1006 (plastic package).
Lead free;RoHS compliant;Halogen free
- Ac`X]b[`7 ca dci bX': `Ua a UW]]hmF UH]b[.
UL 94 V-0
- HYfa]bUg. High temperature soldering guaranteed:
260 °C/10 sec. at terminals

Applications

- Audio Line, Speaker, Headset, Microphone Protection
- Human Interface Devices (Keyboard, Touchpad, Buttons)

5 Vgc`i hY'AU]a i a 'FU]b[g

Ratings at 25 °C, ambient temperature unless otherwise specified

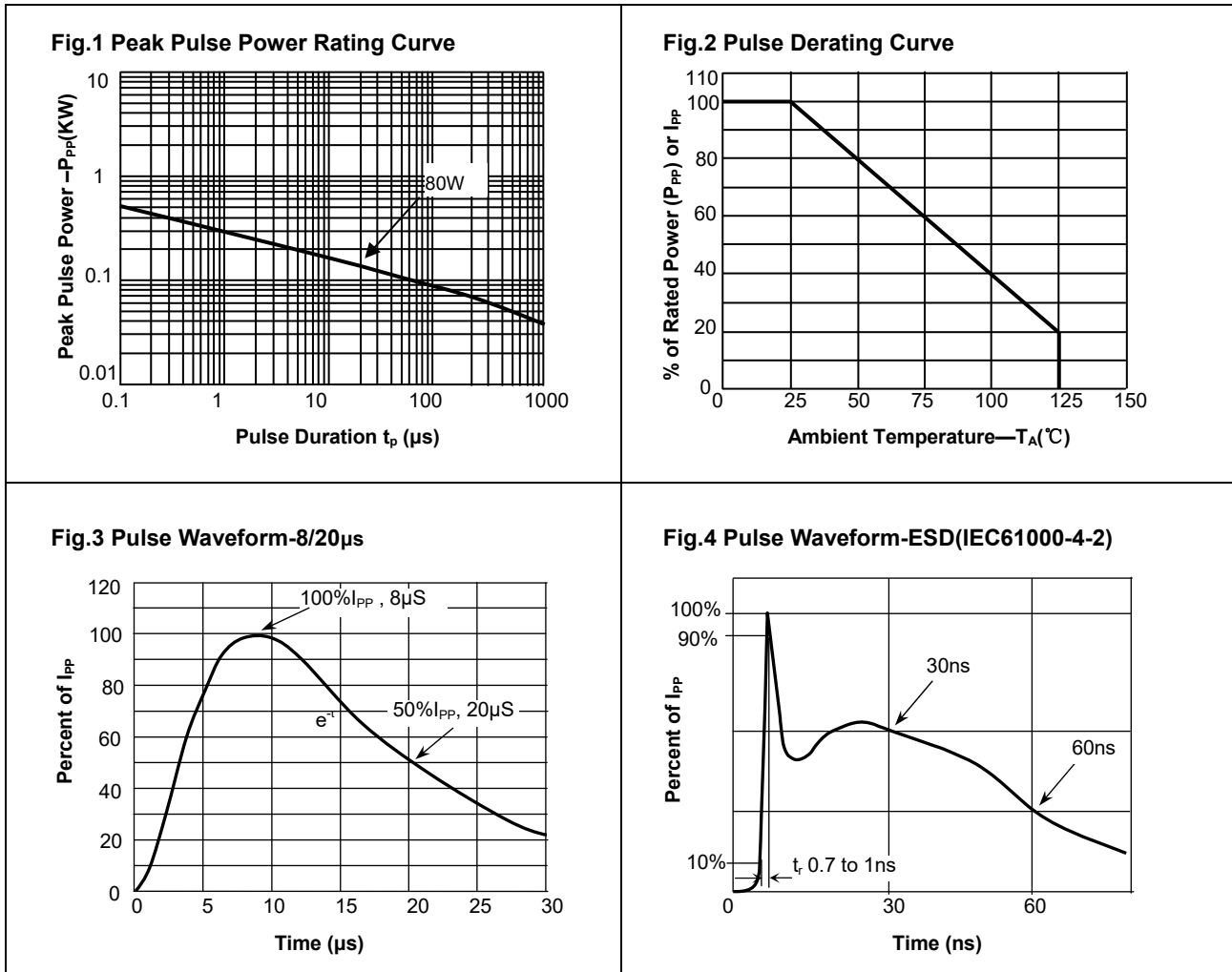
Parameter	Symbol	Value	Unit
Peak Pulse Power ($T_p = 8/20\mu s$)	P_{PP}	80	W
ESD contact/air discharge (IEC-61000-4-2)	V_{ESD}	30/30	kV
Peak Pulse Current ($T_p = 8/20\mu s$)	I_{PP}	7	A
Junction Temperature	T_J	-55 to +150	°C
Storage temperature	T_{STG}	-55 to +150	°C

Electrical Characteristics

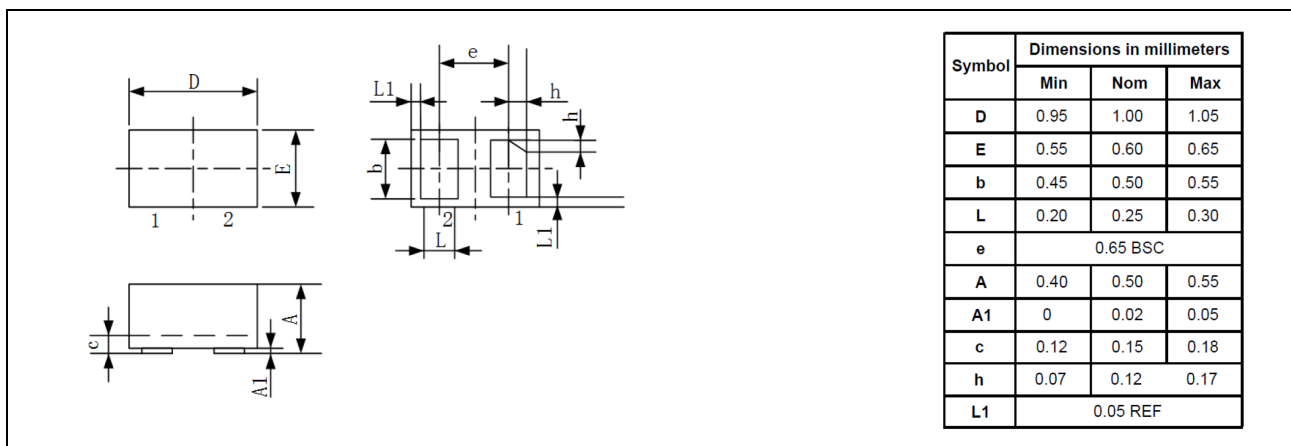
($T_A = 25\text{ °C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Reverse stand-off Voltage	V_{RWM}				7.0	V
Reverse Breakdown Voltage	V_{BR}	$I_T = 1mA$	7.2			V
Reverse Leakage Current	I_R	$V_R = 7V$			1.0	μA
Clamping Voltage (IEC 61000-4-5)	V_C	$I_{PP} = 7A$		10		V
Junction Capacitance	C_J	$V_R = 0V, f = 1MHz$		15		pF

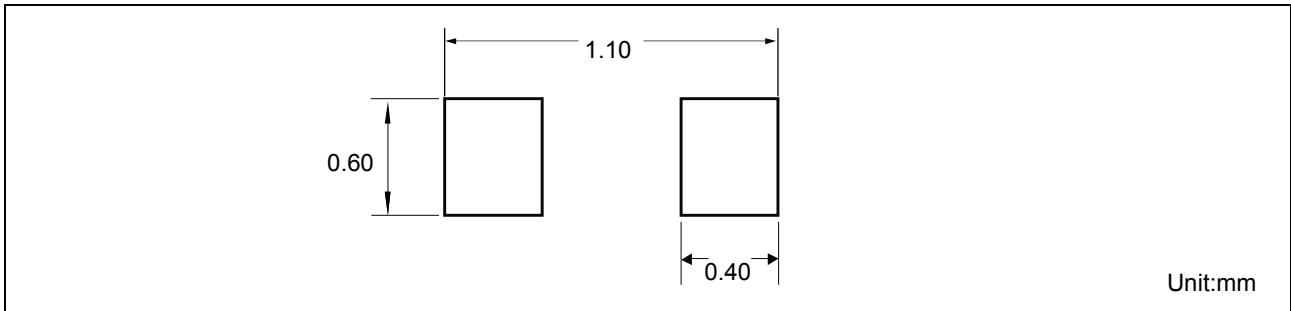
Typical Characteristics ($T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)



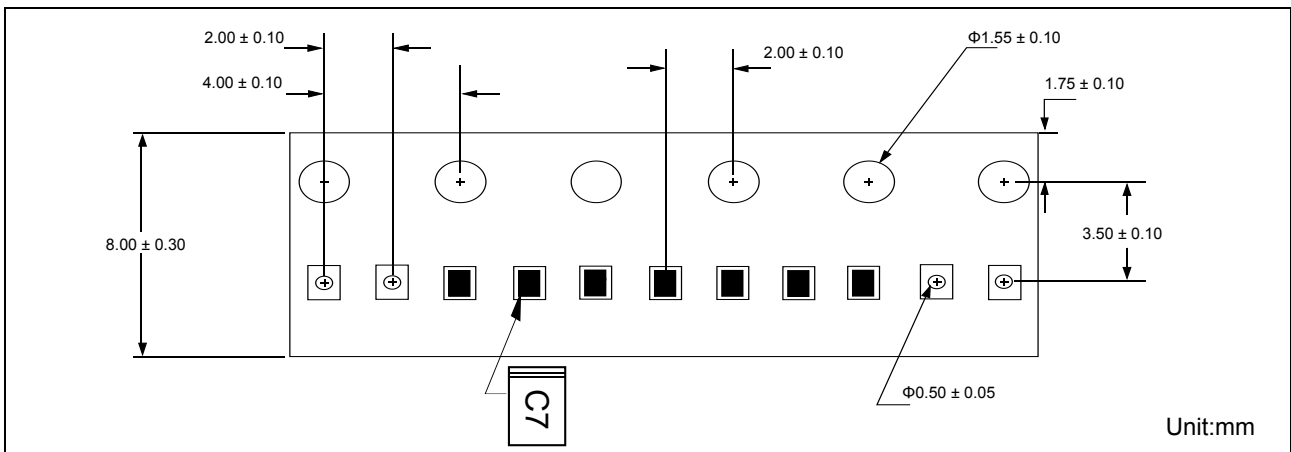
Package Dimensions



Pad Dimensions



Tape and Reel Specification



Ordering information

Order code	Marking	Package	Packaging option	Base quantity	Packaging specification
TESD1006NC7VB	C7	DFN1006	Tape and reel	10000pcs / reel	EIA STD RS-481